## Curriculum and Syllabus for M.Tech.

## Electronics and Communication Engineering With Specialization in Microelectronics and VLSI Systems

From The Academic Year 2021

(Approved by Senate-44)



Indian Institute of Information Technology, Design and Manufacturing, Kancheepuram

Chennai-600 127

		Semester 1					
S.No	Couse Code	Course Name	Category	L	Т	Р	С
1	EC5009	MOSFET Modelling for VLSI Circuits	PCC	3	1	0	4
2	EC5010	Analog IC Design	PCC	3	1	0	4
3	EC5011	VLSI Testing and Testable Design	PCC	3	1	0	4
4		Professional Elective Course 1	PEC	3	1	0	4
5		Professional Elective Course 2	PEC	3	1	0	4
6	EC5012	Device Modelling and Simulation Practice	PCC	0	0	3	1.5
7	EC5013	SoPC and VLSI Testing Practice	PCC	0	0	3	1.5
							23.0
		Semester 2					
S.No	Course Code	Course Name	Category	L	Т	Р	С
1	EC5014	Digital IC Design	PCC	3	1	0	4
2	EC5015	VLSI System Design	PCC	3	1	0	4
3	EC5016	VLSI Technology	PCC	3	1	0	4
4		Professional Elective Course 3	PEC	3	1	0	4
5		Professional Elective Course 4	PEC	3	1	0	4
6	EC5017	IC Design Practice#	PCC	0	0	4	2
7	EC5018	High level verification with System Verilog and UVM\$	РСС	2	0	4	4
\$ - As	per Senate 50,	he credit type was changed from 0 0 3 1.5 to 0 0 4 the course name was changed to High level ver M (2 0 4 4) from Verification Practice (0 0 3 1.5).					26.0
		Semester 3			•	•	•
	Course Code	Course Name	Category	L	Т	Р	С
S.No	Course Code	course nume	category	_			•
S.No 1	EC6003	MT-EC-MVS-Project Phase I (May-July)(Summer Internship)	PCD	0	0	20	10
		MT-EC-MVS-Project Phase I (May-July)(Summer			0	20 32	
1	EC6003	MT-EC-MVS-Project Phase I (May-July)(Summer Internship)	PCD	0			10
1	EC6003	MT-EC-MVS-Project Phase I (May-July)(Summer Internship)	PCD	0			10 16
1	EC6003	MT-EC-MVS-Project Phase I (May-July)(Summer Internship) MT-EC-MVS-Project Phase II (Aug-Nov)	PCD	0			10 16
1 2	EC6003 EC6004	MT-EC-MVS-Project Phase I (May-July)(Summer Internship) MT-EC-MVS-Project Phase II (Aug-Nov) Semester 4	PCD PCD	0	0	32	10 16 26.0

- 1. Professional Elective Course is an elective course offered or prescribed by the parent department.
- 2. 3 Months internship is mandatory, however, the curriculum offers the flexibility to carry out 3-12 Months internship with the approval of the parent department.
- 3. In line with the guidelines approved by the Senate (Senate 46-07), an M.Tech student can earn a maximum of 6 credits from NPTEL Courses. For all successfully completed NPTEL Courses, the letter grade "H" (Pass) will be awarded and credits of such courses will not be accounted for CGPA calculation.

## Semester wise Credit Distribution

Semester							
Category	S1	S2	S3	S4	Total	%	
Professional Core Course (PCC)	15	18	0	0	33	34.1	
Professional Elective Course (PEC)	8	8	0	0	16	18.2	
Professional Career Development (PCD)	0	0	26	16	42	47.7	
Total	23.0	26.0	26.0	16.0	91.0	100.0	
	23.0	49.0	75.0	91.0			

Course Name	MOSFET Modelling for VLSI Circuits	Course Code	EC5009				
Offered by Department	Electronics and Communication EngineeringStructure (LTPC)31			0	4		
To be offered for	M.Tech	Course Type	Core	1	1		
Prerequisite	Basics of Semiconductor Devices, Digital Electronics	Approved In	Senate	-44			
Learning Objectives		<ul> <li>To demonstrate and apply basic concepts of semiconductor physics relevant to devices</li> <li>To describe and use physics-based numerical and analytical device modelling for the inclusion in circuit applications</li> </ul>					
Learning Outcomes	<ul> <li>At the end of the course, the students would be able to</li> <li>Model any kind of MOS Devices in 2-D or 3-D</li> <li>Relate the models for further inclusion in circuits</li> </ul>						
Course Contents (with approximate breakup of hours for lecture/tutorial/ practice)	<ul> <li>Intuitive analysis of MOS Trans Voltage, Surface Condition, Gen Inversion, Small- Signal Capaci</li> <li>Long-Channel MOS Transistor, Models, Weak Inversion Models Mobility (5L+2T)</li> <li>Small-Dimension Effects - Veloc Sharing, Drain-Induced Barrier Ballistic Operation, Polysilicon</li> <li>Small-Dimension Effects-Model Effects; Gate Current, Junction and Properties of Good Models, Extraction, Compact Models, Be</li> <li>Small-Signal Modelling - Condu Circuits, Conductance Paramete Source-Drain and Output Condu Circuits, Capacitance Evaluatio (11L+2T)</li> </ul>	heral Analysis, Invo itance, Three-Term Introduction All-R s, Source Reference city Saturation, Ch c Lowering, Hot Ca Depletion (6L+2L) ling for Circuits Si Leakage, Scaling a Model Formulation enchmark Tests (71 intance Parameter ers Due to Gate an uctance, Capacitan	ersion, St inal MO cegion Mo vs. Body annel Le rrier Effe mulation and New n Conside L+3L) Definition d Body L ce Defini	trong In S Struct odels, St v Referent ength Me ects, Vel - Quant Technol erations ons and c eakage, itions an	version, ure (7L- crong In- nce, Effe odulatio ocity Ov cum-Meo logies, A , Param Equivale Transco nd Equiv	Weak +3T) version ective n, Charge vershoot chanical pproaches, eter ent onductance, valent	
Essential Reading	1. Y. Tsividis and C. McAndrew, M University Press, 2011	IOSFET modelling	for Circ	uit Simı	ulation, (	Oxford	
Supplementary Reading	<ol> <li>BSIM Manuals available on BS</li> <li>T. A. Fjeldly, T. Yetterdal and M Simulation, John Wiley, 1998.</li> <li>Y. Taur and T. H. Ning, Fundar University Press, 1998.</li> <li>Y. P. Tsividis, Mixed Analog-dig Publishing Co Pte Ltd, 2002</li> </ol>	A. Shur, Introducti mentals of Modern	on to De <sup>,</sup> VLSI De	vice Moo vices, C	ambridg	ge	

Course Name	Analog IC Design	Course Code	EC5010				
Offered by Department	Electronics and Communication Engineering	Structure (LTPC)	3	1	0	4	
To be offered for	M.Tech	Course Type	Core				
Prerequisite	NIL	Approved In	Senate	-44			
Learning Objectives	<ul> <li>To impart in depth knowledge design and analysis of operation</li> <li>To be capable of designing an operation</li> </ul>	al amplifiers and o	eircuits u	sing the		e metrics,	
Learning Outcomes	<ul> <li>To analyses effect of mismatch between components in the performance of ICs</li> <li>To model MOSFET in IC</li> <li>To analyses noise in different components in the IC</li> <li>To derive the Data Sheet / Specifications of Single stage, two stage, folded cascad opamps</li> <li>To understand fully differential operation, opamp and make such circuits</li> </ul>						
Course Contents (with approximate breakup of hours for lecture/tutorial/ practice)	<ul> <li>MOS Transistor: Layout, model</li> <li>Noise: Noise in Resistor, capacit</li> <li>Single stage opamp: Noise, offs Analysis in two and higher orde</li> <li>Cascode current mirror, Cascod op amps. (8L+2T)</li> <li>Fully differential circuits and op</li> <li>PLL (6L+2T)</li> </ul>	<ul> <li>Components and mismatch in CMOS process, models and Layout techniques. (4L+2T)</li> <li>MOS Transistor: Layout, model, Body effect, transit frequency. (4L+2T)</li> <li>Noise: Noise in Resistor, capacitor, and MOSFET, spectral density (4L+2T)</li> <li>Single stage opamp: Noise, offset, swing limits and slew rate, Loop gain and stability Analysis in two and higher order opamp (10L+2T)</li> <li>Cascode current mirror, Cascode, Folded Cascode multi stage and Miller compensated op amps. (8L+2T)</li> <li>Fully differential circuits and opamp, common mode feedback circuits. (6L+2T)</li> <li>PLL (6L+2T)</li> <li>Tutorials will include pen-paper analysis and circuit simulation at schematic and</li> </ul>					
Essential Reading	1. Behzad Razavi, Design of Analo Education, 2016, ISBN: 978-0-0		d Circuit	s, 2nd ed	ition Mc	Graw-Hill	
Supplementary Reading	<ol> <li>Tony Chan Carusone, David A. Design, John Wiley &amp; Sons, Inc.</li> <li>Paul R. Gray, Paul J. Hurst, Ste of Analog Integrated Circuits, 5 0-470-24599-6.</li> <li>Tertulien Ndjountche, CMOS A Efficient Design, CRC Press Tay</li> </ol>	., 2012, ISBN: 978- ephen H. Lewis, Ro th edition, John W nalog Integrated C	0-470-77 bert G. N iley & So ircuits H	010-8. Aeyer, An ns, Inc., igh-Spee	nalysis a 2009. IS d and Po	nd Design BN: 978- ower-	

Course Name	VLSI Testing and Testable Design	Course Code	EC5011					
Offered by Department	Electronics and Communication Engineering	Structure (LTPC)	3	1	0	4		
To be offered for	M.Tech	Course Type	Core			·		
Prerequisite	Basics of Digital Electronics	Approved In	Senat	te-44				
Learning Objectives	• The course aims at imparting skills required for the design of an efficient testable circuit and optimal test vectors to detect all faults							
Learning Outcomes	<ul> <li>At the end of the course, the students would be able to</li> <li>Model the faults in the combination and sequential circuits</li> <li>Perform the fault analysis and test pattern generation using ATPG algorithms</li> <li>Build the testable circuit with test vectors.</li> </ul>							
Course Contents (with approximate breakup of hours for lecture/tutorial/ practice)	<ul> <li>Basic of Test and Role of HDL - I System Test, ATE Architecture a</li> <li>Verilog HDL for Design and Test Basic Structures of Verilog, Com bench Techniques. (3L+1T)</li> <li>Fault and Defect Modelling: Fau Related to Gate Level Faults, Fa</li> <li>Fault Simulation Application an Applications, Fault Simulation T</li> <li>Test pattern Generation Method Controllability and Observability</li> <li>Deterministic Test Generation A Methods, Sequential Circuit Tes</li> <li>Design for Test by Means of Scan Full Scan DFT Technique, Scan</li> <li>Standard IEEE Test Access Met Architecture, Boundary Scan Ten RT level Boundary Scan and Bou</li> <li>Logic Built-in Self-test: BIST Ba Analysis, BIST Architectures, R'</li> <li>Test Compression: Test Data Co Decompression Methods. (3L+1T)</li> <li>Memory Testing by Means of Met (2L+1T)</li> </ul>	and Instrumentatio :: Using Verilog in I binational Circuits It Modelling, Struct ult Collapsing in Veri- d Methods: Fault S 'echnologies. (5L+1' s and Algorithm: Ter- v, Random Test Gen- lgorithms: Determining t Generation, Test I and Making circuits Theorem of the constructions, Board and Instructions, Board undary Scan Descrip- sics, Test Pattern O T Level BIST Design mpression, Compre- )	n. Design, , Sequet tural Ga erilog. imulation T) est Gen meration inistic T Data Co Festable RT level an Basic an Basic rd Leve ption La Generati n. (4L- ssion M	(3L+1T) Using V ntial Cir ate Leve (5L+2T) on, Faul eration 7 h. (4L+17) Vest Gen pactic e, Testab Scan D cs, Boun el Scan C anguage ion, Out +1T) Iethods a	Terilog in cuits, T l Faults ) t Simul Basics, Γ) eration m. (4L dary Sca Chain St . (5L+27 put Res and	n Test, est ation +1T) sertion, 4L+2T) an tructure, Γ) ponse		
Essential Reading	1. ZainalabedinNavabi, Test and T Architecture, 1 <sup>st</sup> edition, Springe							
Supplementary Reading	<ol> <li>M. Abramovici, M. A. Breuer and Testable Design, Wiley-IEEE Pr</li> <li>Niraj K. Jha, Sandeep Gupta, Te University Press, 2003. ISBN: 03</li> <li>Michael L. Bushnell, Vishwani I Digital, Memory, and Mixed-Sign 7991-8.</li> </ol>	ess, 1994, ISBN: 97 sting of Digital Sys 521-77356-3 ). Agrawal, Essenti	8-0-780 stems, 1 als of E	93-1062-9 st editio	9. m, Cam c Testin	bridge g for		

Course Code	Device Modelling and Simulation Practice	Course Code	EC5012				
Offered by Department	Electronics and Communication Engineering	Structure (LTPC)	0	0 0 3 1.5			
To be offered for	M.Tech	Course Type	Core				
Prerequisite	NIL	Approved In	Senate	-44			
Learning Objectives		semiconductor device	ice mode structur				
Learning Outcomes	<ul> <li>At the end of the course, students would be able to:</li> <li>simulate and analyse structure, doping profile, terminal characteristics and distributions of carriers, current, field, potential and energy band diagrams within 2-dimensional device structures</li> </ul>						
Course Contents (with approximate breakup of hours for lecture/tutorial/ practice)	<ul> <li>Introduction to Technology com device and process simulations.</li> <li>Device simulation: observing th current, field, potential and ene</li> <li>Process simulation: observation</li> <li>Simulation of 2-D MOSFETs th</li> <li>Simulation of novel 3-D transist devices, solar cells etc, through</li> <li>DC, AC, RF mixed mode and no</li> </ul>	e terminal characte orgy band diagrams of device structure rough device and p tors such as III-V H device simulation	eristics a within t and dop rocess sin IEMT, L	nd distri he device ving profi mulation EDs, Fin	butions o e. le is	of carriers,	
Essential Reading	<ol> <li>C K Maiti, "Introducing Technology Computer-Aided Design (TCAD): Fundamentals, Simulations, and Applications", Jenny Stanford Publishing; 1<sup>st</sup> Edition, 2017, ISBN: 978-9814745512.</li> <li>Wu, Yung-Chun, Jhan, Yi-Ruei, "3D TCAD Simulation for CMOS Nanoeletronic Devices", Springer, 2017, ISBN 978-981-10-3066-6.</li> </ol>					7, ISBN:	
Supplementary Reading	<ol> <li>C K Sarkar, "Technology Compu- CRC Press, 1<sup>st</sup> Edition, 2013, IS</li> <li>JP. Colinge, "FinFETs and Otl 978-0-387-71751-7</li> <li>TCAD Manual (Available Onlin</li> </ol>	BN: 978-14665126 her Multi-Gate Tra	58.				

Course Name	SoPC and VLSI Testing Practice	Course Code	EC501	3				
Offered by Department	Electronics and Communication Engineering	Structure (LTPC)	0	0	3	1.5		
To be offered for	M. Tech	Course Type	Core	•		•		
Prerequisite	NIL	Approved In	Senate	-44				
Learning Objectives	Design and development complete har	rdware/software sys	stem on I	FPGA an	d VLSI	testing		
Learning Outcomes	able to effectively use commercially a integrated systems, can able to efficie	Student can able to design and develop the hardware/software system on FPGA, can able to effectively use commercially available building block (IP) to construct highly integrated systems, can able to efficiently break down complex computational tasks into hardware and software components and build co-processor.						
Course Contents (with approximate breakup of hours for lecture/tutorial/ practice)	<ul> <li>Scan Chain based Sequential Circuit Testing</li> <li>Fault Models simulations and verifications, Structural Testing with Fault Models</li> <li>Implement path delay fault testing</li> </ul>							
Essential Reading	<ol> <li>Wang, "VLSI Test Principles and Architectures: Design for Testability", Elsevier; First edition (1 January 2011). ISBN: 9380501552</li> <li>Louise H. Crockett, Ross A. Elliot, Martin A. Enderwitz, Robert W. Stewart, The Zynq Book: Embedded Processing with the ARM Cortex-A9 on the Xilinx Zynq- 7000 All, 1<sup>st</sup> edition, Strathclyde Academic Media, 2014. ISBN: 099297870X.</li> </ol>					art, The vnq-		
Supplementary Reading	<ol> <li>Wayne Wolf, FPGA based Syste 0131424610.</li> <li>2. Steve Furber, ARM System o 2000. ISBN: 0201675196.</li> </ol>	-						

Course Name	Digital IC Design	Course Code	EC5014			
Offered by Department	Electronics and Communication Engineering	Structure (LTPC)	3	1	0	4
To be offered for	M Tech	Course Type	Core			
Prerequisite	NIL	Approved In	Senate	-44		
Learning Objectives	<ul> <li>To impart in depth knowledge in CMOS digital circuits, performance metrics, design procedures for complex combinational and sequential circuits and subsystems.</li> <li>Students would be able to design and analyse complex digital integrated circuits usin semicustom and full custom design procedures.</li> </ul>					
Learning Outcomes	<ul><li>using tool for higher level</li><li>To model MOSFETs and Interco</li><li>To determine Noise margins, sw</li></ul>	OSFETs and Interconnects in ICs e Noise margins, switching voltage, delay parameters, power etc. in ICs ombinational and sequential circuits with static and dynamic CMOS and tors				
Course Contents (with approximate breakup of hours for lecture/ tutorial/practice)	<ul> <li>Issues in Digital Integrated Circuit Design (1L)</li> <li>Fabrication of CMOS IC and packaging (4L+1T)</li> <li>MOS Device: Threshold Voltage, Secondary Effects, SPICE Models (4L+2T)</li> <li>Interconnect: Parameters, Electrical Wire Models, SPICE Wire Models (2L+1T)</li> <li>CMOS Inverter: Transfer Characteristics, Noise margin, Capacitances, Propagation Delay, Power (5L+2T)</li> <li>Combinational Logic Circuits: Static CMOS, Pass-Transistors, Dynamic CMOS, Dynamic Logic, Cascading (7L+2T)</li> <li>Sequential Logic Circuits: Timing Metrics, Static and Dynamic Latches, Registers, C2MOS, NORA-CMOS (7L+2T)</li> <li>Arithmetic Building Blocks: Data paths in Digital Processor Architectures (7L+2T)</li> <li>Memory and Array Structures: ROM, RAM, CAM, Peripheral Circuitry, PLA and Flash Memory (5L+2T)</li> <li>Tutorials will include pen-paper analysis and circuit simulation at schematic and layout level</li> </ul>					
Essential Reading	1. Jan M. Rabaey, Anantha Chand 2nd edition, Pearson, 2003. ISB					
Supplementary Reading	<ol> <li>John E. Ayers, Digital Integrate Press, 2009. ISBN-10: 14200698</li> <li>R. Jacob Baker, CMOS Circuit I Blackwell, 2010. ISBN-10: 0470</li> <li>Sung-Mo (Steve) Kang, Yusuf L Circuits Analysis &amp; Design, 4th 10: 0073380628, ISBN-13: 978-0</li> </ol>	87X, ISBN-13: 978- Design, Layout, and 1881321, ISBN-13: 9 eblebici, Chilwoo K edition, McGraw-F	1420069 d Simula 978-0470 fim, CM(	877. tion, 3rd 881323. OS Digita	edition, al Integra	Wiley- ated

Course Name	VLSI System Design	Course Code	EC501	5				
Offered by Department	Electronics and Communication Engineering	Structure (LTPC)	3	1	0	4		
To be offered for	M.Tech	Course Type	Core					
Prerequisite	NIL	Approved In	Senate	-44				
Learning Objectives		To impart in depth knowledge in the design, simulation and analyses of complex VLSI circuits including both digital and analog building blocks.						
Learning Outcomes	<ul> <li>Understand circuits and syst integrated circuits</li> <li>Design and analyze complex verification tools</li> </ul>	<ul> <li>integrated circuits</li> <li>Design and analyze complex VLSI systems using industry level design and verification tools</li> </ul>						
Course Contents (with approximate breakup of hours for lecture/tutorial/ practice)	<ul> <li>Review of VLSI, Classification implementation options of VL Modeling Styles (L5+1T)</li> <li>Designing Fast CMOS Circus Effort and Optimization, Low Techniques at Circuit and Sy mitigation Techniques. (L8+7)</li> <li>VLSI system design with HD dataflow, structural and mix designs. Data path subsyster arithmetic circuits and interva and design verification inclue</li> <li>Interconnect Design: Design Parasitic, Interconnect Techn Distribution Networks, Clock Designs: Design consideration reliability. (L7+T2)</li> <li>Input/output Modules and ESD Drivers, and ESD Protection (L5+T2)</li> </ul>	SI Systems. Y-Cha its, Various Techni v Power Design Te zstem Levels, Trad T3) DL: Module concept ed style modeling, n design: Combina connects; implemen ding post layout sin issues with Resist niques, Power Dist & Generation and I ons for signal integr	rt, Design iques for I chniques, eoffs in Po s and moo Synthesis tional and ntation of mulations ive, Capac ribution a Distributio rity, manu works: Inp	Abstract Delay Es Power M ower & I deling st and ver such sys . (L7+T2 citive an nd Clock on Netwo ifactura	ction Leve stimation Managem Delay and cyles: Beh rification atial circu stems wit 2) d Inducti k Design: orks, Lay bility and ers, Outp	els. , Logical ent 1 avioral, of its, ch HDL ve Power out 1 ut		
Essential Reading	Ming-Bo Lin, Introduction to VLSI S Press, 2012, ISBN:978-1-4398-6859.	ystems A logic, cir	cuit and S	ystems	Perspect	ive, CRC		
Supplementary Reading	<ol> <li>Neil H. E. Weste, David Money J Perspective, 4<sup>th</sup> edition, Addison</li> <li>Liming Xiu, VLSI Circuit Design IEEE Press, A John Wiley &amp; Son</li> <li>Hubert Kaeslin, Morgan Kaufma ISBN: 978-0-12-800730-3.</li> </ol>	-Wesley, Pearson, n, Methodology De ns, Inc., 2008, ISBI	2013, ISB mystified, N:978-0-4'	N:978-0 A conce 70-1274:	-321-547 ptual Ta: 2-1.	74-3. xonomy,		

Course Name	VLSI Technology	Course Code	EC5016					
Offered by Department	Electronics and Communication Engineering	Structure (LTPC)	3	1	0	4		
To be offered for	M.Tech	Course Type	Core	Core				
Prerequisite	NIL	Approved In	Senate	<b>e-</b> 44				
Learning Objectives		<ul> <li>To offer a profound understanding of the design of complex VLSI devices, and</li> </ul>						
Learning Outcomes	<ul> <li>Appreciate the intricacies invol</li> <li>Understand the various process</li> </ul>	• Understand the various processes needed to fabricate the VLSI devices.						
Course Contents (with approximate breakup of hours for lecture/tutorial/ practice)	<ul> <li>Introduction to VLSI Design, B Fabrication. (L4+T1)</li> <li>Crystal Structure of Si, Defects</li> <li>Epitaxy, Vapour phase Epitaxy (L4+T1)</li> <li>Oxidation – Kinetics, Rate cons (L5+T2)</li> <li>Diffusion-Theory of Diffusion, I - Process, Annealing of Damage</li> <li>Lithography, immersion lithogr Etching-Wet Chemical Etching other materials (L3+T1)</li> <li>Deposition-Plasma Deposition, contacts, Copper interconnects</li> <li>IC BJT - LOCOS, Trench isolat for high-speed applications (L3- MOSFET - Metal gate vs. Self-a CMOS Technology, Latch - up i channels and high-k gate dieled</li> </ul>	in Crystal, Crystal , Doping during Ep tants, Dopant Redi Doping Profiles, Diff es, Masking during raphy, e-beam litho , Dry Etching, Plass Metallization, Prob (L4+T1) ion, Poly-emitter-pa +T1) aligned Poly-gate, T n CMOS, MOSFET	growth itaxy, M stributio fusion Sy Implant graphy ( ma Etchi lems in bly-base- ailoring	(L3+T1) olecular on, Oxide vstems Ic ation (L5 L5+T2) ing, Si, S Aluminiu BJT and of Device res with	beam Ej Charge on Impla +T2) iO <sub>2</sub> , SiN um Meta its suit e Param strained	pitaxy s antation V and al ability neters,		
Essential Reading	S. K. Ghandhi, VLSI Fabrication Prin	nciples- Silicon and	Galium	Arsenide	e, John			
Supplementary Reading	<ol> <li>S. M. Sze, VLSI Technology, Ta</li> <li>J. Plummer, M. D. Deal, P. B. O Practice and Modelling, Pearso</li> </ol>	Friffin, Silicon VLS	[ Techno	logy, Fur	ndamen	tals,		

Course Name	IC Design Practice#	Course Code	EC5017				
Offered by Department	Electronics and Communication Engineering	Structure (LTPC)	0 0 4 2				
To be offered for	M Tech	Course Type	Core				
Prerequisite	NIL	Approved In	Senate	-44			
Learning Objectives	analog integrated circuits espec amplifiers and Digital integrate	ially operational ar ed circuits. n and analyse comp	nplifiers plex anal	lex analog and digital integrated			
Learning Outcomes	<ul> <li>To be capable of simulating Schematic level analog circuits with at least 20+ transistors</li> <li>To be capable of generating layout with full custom / semicustom tools and to perform post layout simulations and extracting parameters to schematic model</li> <li>To design Digital building blocks using VHDL / Verilog</li> <li>To generate synthesizable design, create layout and post layout simulations for ASIC Design</li> </ul>					o perform	
Course Contents (with approximate breakup of hours for lecture/tutorial/ practice)	<ul> <li>Design of analog ICs with Scher Synopsys tools (6 weeks)</li> <li>Design of digital building blocks and Synopsys tools (6 weeks)</li> <li>Project will include identifying a IEEETCASI, IEEE TCASII, IEI MWCAS, simulate both schema</li> </ul>	s with Schematic ar analog / digital IC f EE TBioCAS, ISCA	nd layou from pap S, ISICA	t simula ers of IE AS, NEW	tion usin CEE JSSC 'CAS, AF	g Cadence C,	
Essential Reading	<ol> <li>Behzad Razavi, Design of Analo Education, 2016, ISBN: 978-0-0</li> <li>Jan M. Rabaey, Anantha Chano 2<sup>nd</sup> edition, Pearson, 2003, ISBN</li> </ol>	7-252493-2 drakasan, Borivoje	Nikolic,	Digital I	ntegrate	d Circuits,	
Supplementary Reading	<ul> <li>Design, John Wiley &amp; Sons, Inc</li> <li>Paul R. Gray, Paul J. Hurst, Ste Of Analog Integrated Circuits, 8 0- 470-24599-6</li> <li>Sung-Mo (Steve) Kang, Yusuf L Circuits Analysis &amp; Design, 4th 10: 0073380628.</li> </ul>	A. Johns, Kenneth W. Martin, Analog Integrated Circuit Inc., 2012, ISBN: 978-0-470-77010-8. Stephen H. Lewis, Robert G. Meyer, Analysis and Design as, 5th edition, John Wiley & Sons, Inc., 2009. ISBN: 978- of Leblebici, Chilwoo Kim, CMOS Digital Integrated 4th edition, Mcgraw-Hill Higher Education, 2014. ISBN- grated Circuit Design Using Verilog and System Verilog, 5BN: 978-0-12-408059-1.					

Course Name	High level verification with System Verilog and UVM\$	Course Code	EC5018					
Offered By Department	Electronics and Communication Engineering	Structure (LTPC)	2	0	4	4		
To be offered for	M. Tech	Course Type	Core		•			
Prerequisite	Hold on Digital Logic Design, and HDL with design flow of VLSI Systems	Approved In	Senate	-44				
Learning Objectives		To impart in depth knowledge and hands-on on the Design, Simulation and Verification Flow of Digital Circuits & Systems. Analyses of complex VLSI circuits including both digital and analog building blocks.						
Learning Outcomes	Students would be able to design and level Design and verification tools.	analyse complex V	LSI syst	ems usin	g indust	ry		
Course Contents (with approximate breakup of hours for lecture/tutorial/ practice)	<ul> <li>Understand and use the System including new data types, litera relaxation of Verilog language r tasks and functions, new hierar clocking blocks, assertions, cove</li> <li>Generate &amp; analyse functional of coverage</li> <li>Basic UVM constructs &amp; classes</li> <li>System Verilog/HDL verification stimulus, coverage, strings, que these features for more effective</li> <li>Power and Clock Routing, Inter</li> </ul>	<ul> <li>Understand and use the System Verilog/HDL RTL design and synthesis features, including new data types, literals, procedural blocks, statements, and operators, relaxation of Verilog language rules, fixes for synthesis issues, enhancements to tasks and functions, new hierarchy and connectivity features, and interfaces, clocking blocks, assertions, cover. Verify the design to ensure 100% coverage.</li> <li>Generate &amp; analyse functional coverage, code coverage, line coverage &amp; FSM coverage</li> <li>Basic UVM constructs &amp; classes, design a basic test environment using UVM</li> <li>System Verilog/HDL verification features, including classes, constrained random stimulus, coverage, strings, queues and dynamic arrays, and learn how to utilize these features for more effective and efficient verification.</li> <li>Power and Clock Routing, Interconnects design considerations</li> <li>Floor planning, placement &amp; Routing of the Digital Blocks, physical fixes and</li> </ul>						
Essential Reading	<ol> <li>Ming-Bo Lin, Introduction to VI Perspective, CRC Press, 2012, I</li> <li>System Verilog for Design: A Gu Design and Modelling, 2<sup>nd</sup> Edition</li> </ol>	SBN:978-1-4398-68 aide to Using Syste	359. m Verilo	g for Hai				
Supplementary Reading	<ol> <li>Chris Spear, System Verilog for Verification: A Guide to Learning the Testbench Language Features, Springer. 2012, ISBBN: 978-1461407140.</li> <li>Donald Thomas, Logic Design and Verification Using System Verilog, 2016, ISBN: 1523364025.</li> <li>UVM Primer: A Step-by-Step Introduction to the Universal Verification Methodology, 2013, ISBN: 0974164933.</li> </ol>					ench		